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Team Nexperia



# PMBTA45

500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

Rev. 02 — 10 March 2010 Product data she Product data sheet

#### **Product profile** 1.

#### 1.1 General description

NPN high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9050T.

#### 1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified

#### 1.3 Applications

- Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	500	V
$V_{CEO}$	collector-emitter voltage	open base	-	-	500	V
I <sub>C</sub>	collector current		-	-	0.15	Α
h <sub>FE</sub>	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 30 \text{ mA}$	50	100	-	



### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 2. Pinning information

Table 2. Pinning

Iddic 2.	ı ııııııg		
Pin	Description	Simplified outline	Graphic symbol
1	base		_
2	emitter		3 
3	collector	1 2	1 — 2
			svm021

### 3. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
PMBTA45	-	plastic surface-mounted package; 3 leads	SOT23				

### 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMBTA45	LK*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

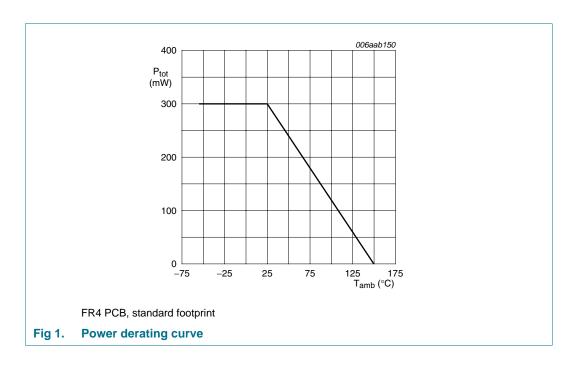
### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 5. Limiting values

**Table 5.** Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	500	V
$V_{CEO}$	collector-emitter voltage	open base	-	500	V
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	500	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	0.15	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	0.5	Α
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



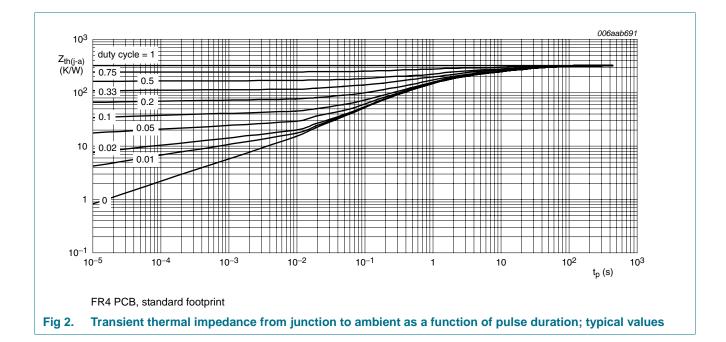
### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	M	in	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _		-	417	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-		-	70	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 7. Characteristics

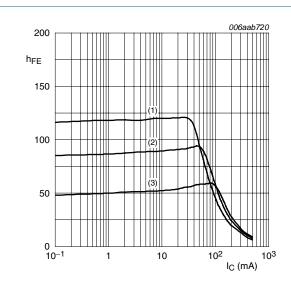
**Table 7. Characteristics** 

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$I_{CBO}$	collector-base cut-off	$V_{CB} = 360 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
current		$V_{CB} = 360 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 ^{\circ}\text{C}$		-	-	10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 360 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V					
		$I_C = 30 \text{ mA}$		50	100	-	
		$I_C = 50 \text{ mA}$	[1]	50	100	-	
V <sub>CEsat</sub>	collector-emitter	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$		-	60	75	mV
	saturation voltage	$I_C = 50 \text{ mA}; I_B = 6 \text{ mA}$	[1]	-	65	90	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	[1]	-	0.75	0.9	V
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{E} = 10 \text{ mA};$ f = 100 MHz		-	35	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	4	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V};$ $I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$		-	200	-	pF
t <sub>d</sub>	delay time	$V_{CC} = 20 \text{ V}; I_C = 0.05 \text{ A};$		-	80	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = 5 \text{ mA};$ $I_{Boff} = -10 \text{ mA}$		-	2700	-	ns
t <sub>on</sub>	turn-on time			-	2780	-	ns
t <sub>s</sub>	storage time			-	3400	-	ns
t <sub>f</sub>	fall time			-	800	-	ns
t <sub>off</sub>	turn-off time			-	4200	-	ns

<sup>[1]</sup> Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

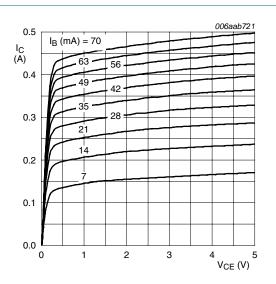
#### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor



 $V_{CE} = 10 \text{ V}$ 

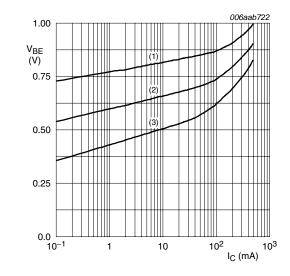
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

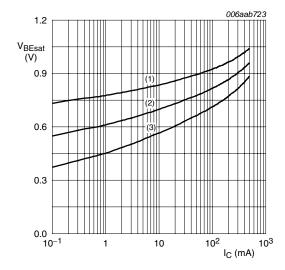
Fig 4. Collector current as a function of collector-emitter voltage; typical values



V<sub>CE</sub> = 10 V

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

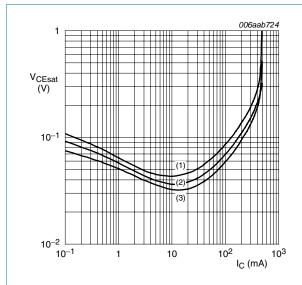


 $I_{\rm C}/I_{\rm B}=5$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

#### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor



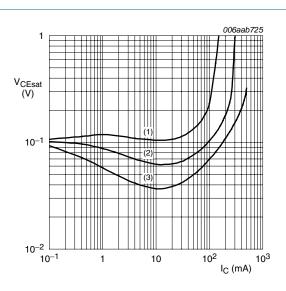
$$I_{\rm C}/I_{\rm B}=5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



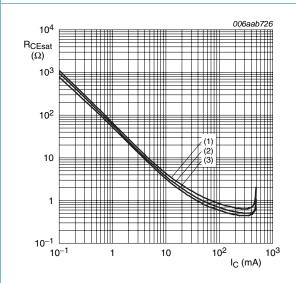
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3)  $I_C/I_B = 5$ 

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



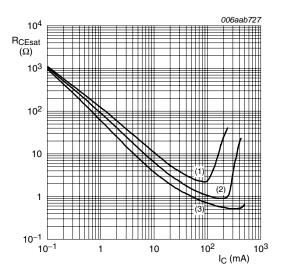
$$I_{\rm C}/I_{\rm B}=5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 20$$

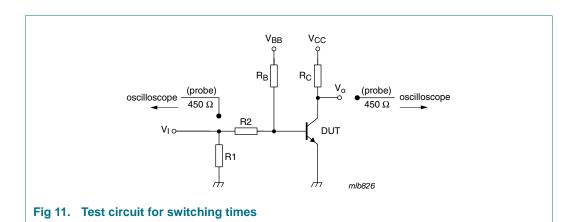
(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

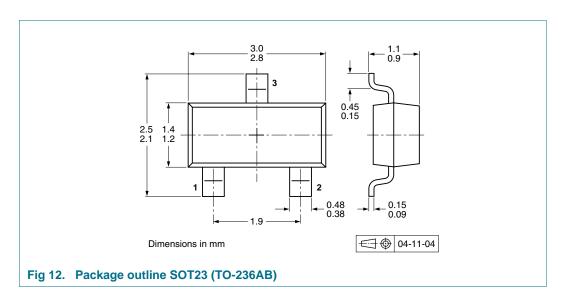
#### 8. Test information



#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



# 10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMBTA45	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 14.

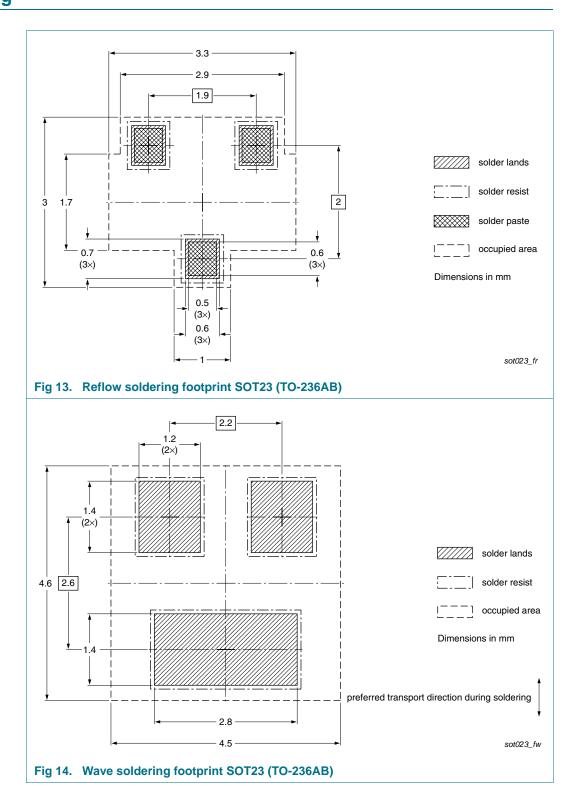
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### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 11. Soldering



### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 12. Revision history

#### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA45_2	20100310	Product data sheet	-	PMBTA45_1
Modifications:	• Figure 7: upo	dated		
PMBTA45_1	20090916	Product data sheet	-	-

#### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PMBTA45 **NXP Semiconductors** 

### 500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

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